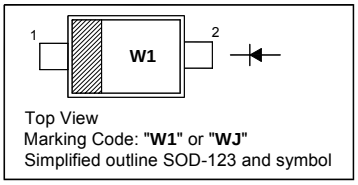
1N914W

Silicon Epitaxial Planar Switching Diode

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Top View
Marking Code: "**W1**" or "**WJ**"
Simplified outline SOD-123 and symbol

Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Repetitive Reverse Voltage	V_{RRM}	100	V
Average Rectified Forward Current	$I_{F(AV)}$	200	mA
Non-repetitive Peak Forward Surge Current at t = 1 s at t = 1 µs	I_{FSM}	1 2	A
Power Dissipation	P_{tot}	400	mW
Thermal Resistance from Junction to Ambient Air	$R_{\theta JA}$	312	°C/W
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	- 55 to + 150	°C

Electrical Characteristics (T_a = 25 °C)

Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at I_F = 10 mA	V_F	-	1	V
Reverse Breakdown Voltage at I_R = 5 µA at I_R = 100 µA	 $V_{(BR)R}$ $V_{(BR)R}$	 75 100	 - -	 V V
Reverse Current at V_R = 20 V at V_R = 75 V at V_R = 20 V, T_j = 150 °C	I_R	 - - -	 25 5 50	 nA µA µA
Capacitance at V_R = 0 V, f = 1 MHz	C_{tot}	-	4	pF
Reverse Recovery Time at I_F = I_R = 30 mA, I_{rr} = 3 mA, R_L = 100 Ω	t_{rr}	-	50	ns

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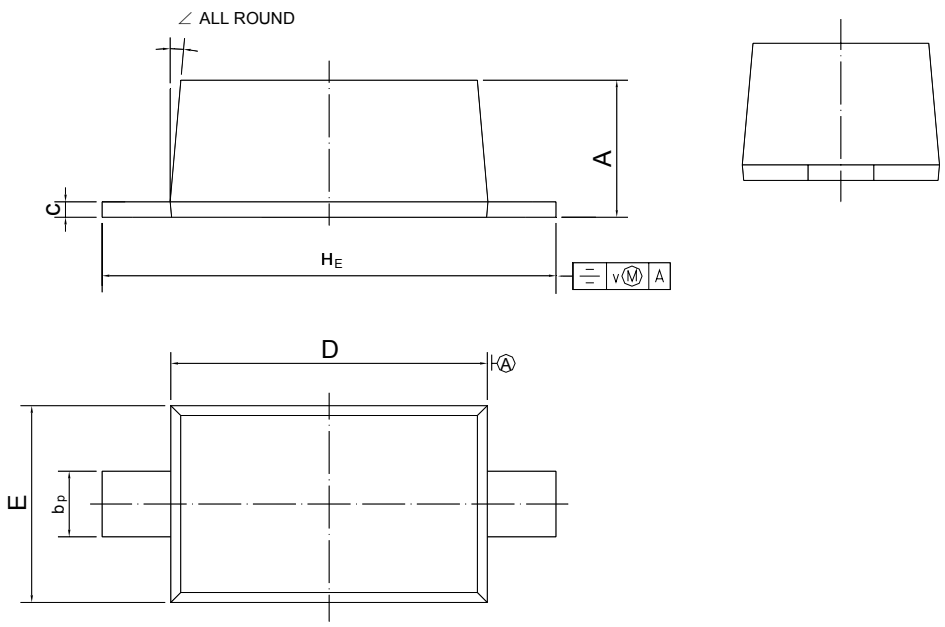
PACKAGE OUTLINE

Plastic surface mounted package; 2 leads **SOD-123**



UNIT	A	b_p	c	D	E	H_E	v	∠
mm	1.15 1.05	0.6 0.5	0.135 0.100	2.7 2.6	1.65 1.55	3.85 3.55	0.2	5°